



US 20240237342A1

(19) **United States**

(12) **Patent Application Publication**
LEE et al.

(10) **Pub. No.: US 2024/0237342 A1**

(43) **Pub. Date: Jul. 11, 2024**

(54) **SEMICONDUCTOR MEMORY DEVICE AND
METHOD OF MANUFACTURING THE
SEMICONDUCTOR MEMORY DEVICE**

H10B 41/35 (2006.01)

H10B 43/35 (2006.01)

(52) **U.S. CL.**

CPC *H10B 43/27* (2023.02); *H10B 41/27*
(2023.02); *H10B 41/35* (2023.02); *H10B*
43/35 (2023.02)

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(21) Appl. No.: **18/349,735**

(22) Filed: **Jul. 10, 2023**

(30) **Foreign Application Priority Data**

Jan. 10, 2023 (KR) 10-2023-0003453

Publication Classification

(51) **Int. CL.**

H10B 43/27 (2006.01)

H10B 41/27 (2006.01)

(57)

ABSTRACT

A semiconductor memory device and a method of manufacturing the semiconductor memory device are provided. The semiconductor memory device includes a first stacked structure including a plurality of first electrode patterns and a plurality of first interlayer insulating layers that are alternately stacked on each other, a first vertical structure extending into the first stacked structure in a vertical direction, an insulating layer formed over the first stacked structure, a coupling structure passing through the insulating layer and formed over the first vertical structure, a second stacked structure including a plurality of second electrode patterns and a plurality of second interlayer insulating layers that are alternately stacked on each other over the insulating layer, and a second vertical structure extending into the second stacked structure in the vertical direction and formed over the coupling structure.

